ALPHA & OMEGA SEMICONDUCTOR

AONP36332U

30V Dual Asymmetric N-Channel MOSFET

General Description

- Bottom source technology
- Very Low $R_{DS(ON)}$ at Vgs 4.5V
- Low Gate Charge
- High Current Capability
- RoHS 2.0 and Halogen-Free Compliant

Applications

- Buck-boost Converters in Computing
- Point of Load Converter
- See Note H

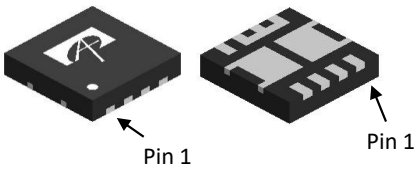
Product Summary

	Q1	Q2
V_{DS}	30V	30V
I_D (at V_{GS}=10V)	97A	60A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 3.5mΩ	< 4.4mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 4.5mΩ	< 5.6mΩ

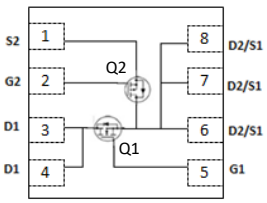
100% UIS Tested
100% Rg Tested

GREEN Product

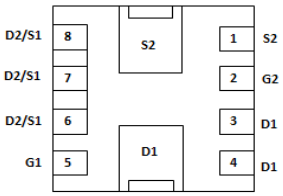
DFN3.3x3.3D



Top View



Bottom View



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONP36332U	DFN3.3x3.3D	Tape & Reel	3000

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage		V_{DS}	30	30	V
Gate-Source Voltage		V_{GS}	±12	±12	V
Continuous Drain Current	T_C=25°C	I_D	97	60	A
	T_C=100°C		61	37	
Pulsed Drain Current [C]		I_{DM}	150	127	
Continuous Drain Current	T_A=25°C	I_{DSM}	24	20	A
	T_A=70°C		20	16	
Avalanche Current [C]		I_{AS}	60	49	A
Avalanche energy	L=0.01mH	E_{AS}	18	12	mJ
Power Dissipation [B]	T_C=25°C	P_D	52	26	W
	T_C=100°C		21	10	
Power Dissipation [A]	T_A=25°C	P_{DSM}	3.4	3.1	W
	T_A=70°C		2.2	2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient [A]	$R_{\theta JA}$	30	33	36	40	°C/W
Maximum Junction-to-Ambient [A D]		52	55	63	66	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1.9	3.8	2.4	4.8	°C/W

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±12V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	1.1	1.5	1.9	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		2.9	3.5	mΩ
		T_J=125°C		4.2	5.1	
		V_{GS}=4.5V, I_D=20A		3.5	4.5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		108		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				60	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		1520		pF
C_{oss}	Output Capacitance			330		pF
C_{rss}	Reverse Transfer Capacitance			35		pF
R_g	Gate resistance	f=1MHz	0.4	0.8	1.2	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=20A		22	40	nC
Q_g(4.5V)	Total Gate Charge			10	20	nC
Q_{gs}	Gate Source Charge			4		nC
Q_{gd}	Gate Drain Charge			2.2		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		6		ns
t_r	Turn-On Rise Time			2.5		ns
$t_{D(off)}$	Turn-Off DelayTime			22		ns
t_f	Turn-Off Fall Time			2		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, di/dt=500A/µs		12		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, di/dt=500A/µs		21		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.
H. For application requiring slow >1ms turn-on/turn-off, please consult AOS FAE for proper product selection.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

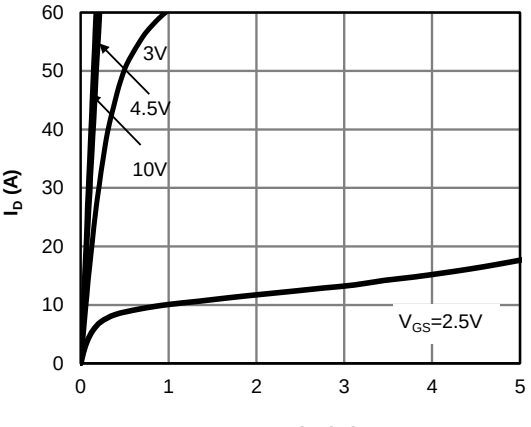


Figure 1: On-Region Characteristics (Note E)

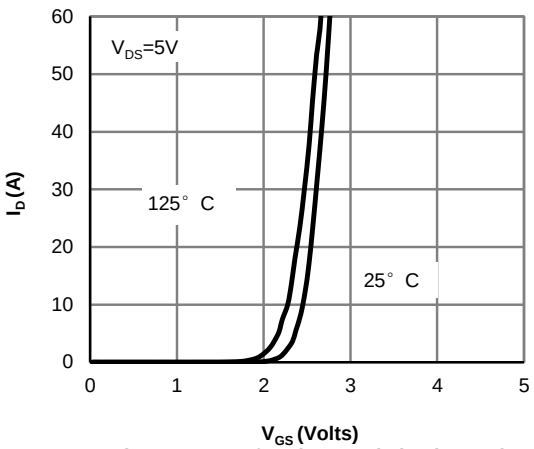


Figure 2: Transfer Characteristics (Note E)

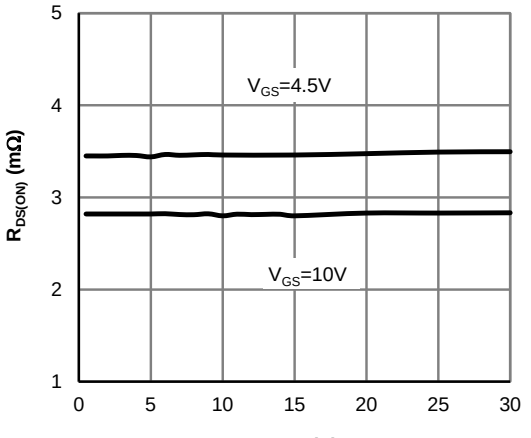


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

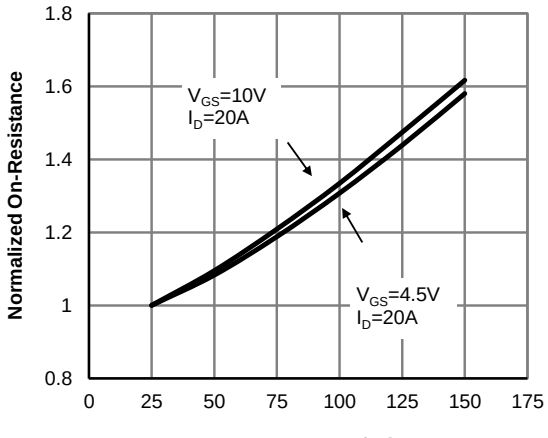


Figure 4: On-Resistance vs. Junction Temperature (Note E)

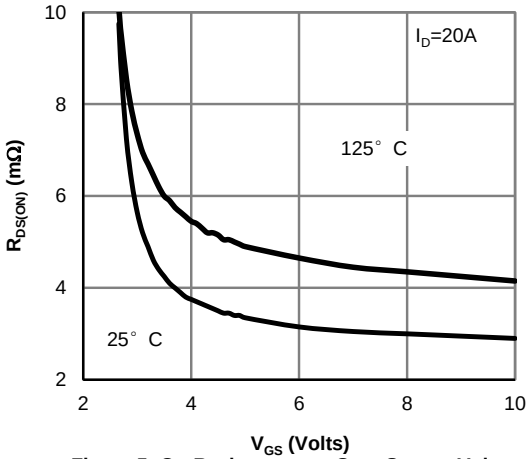


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

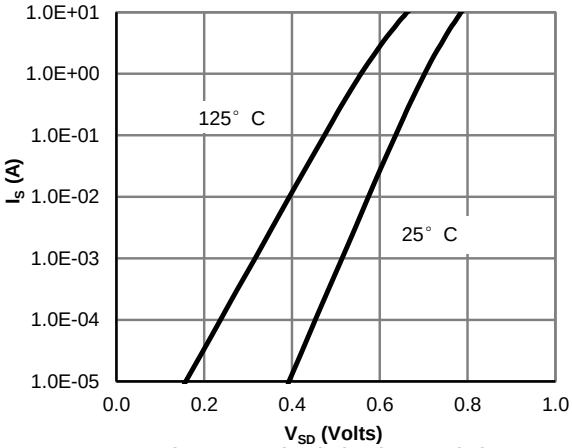


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

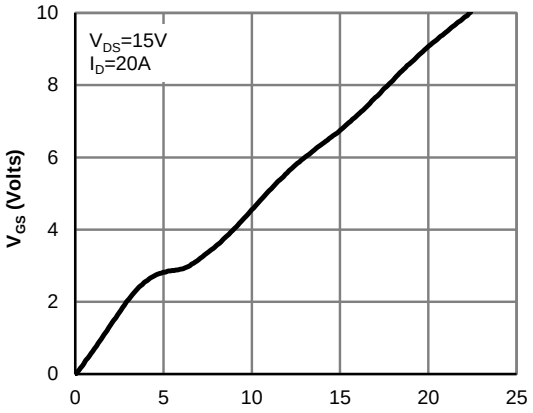


Figure 7: Gate-Charge Characteristics

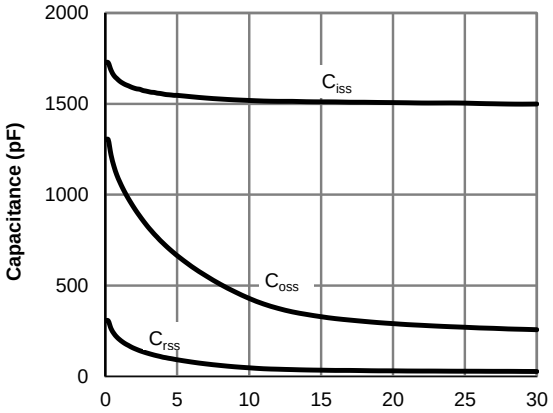


Figure 8: Capacitance Characteristics

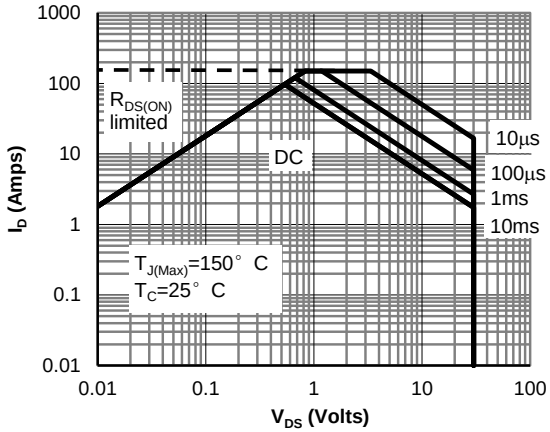


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

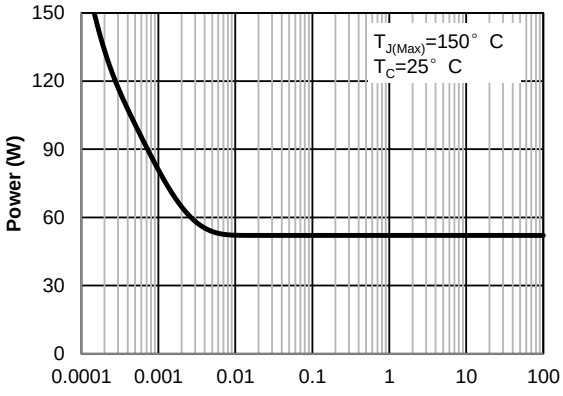


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

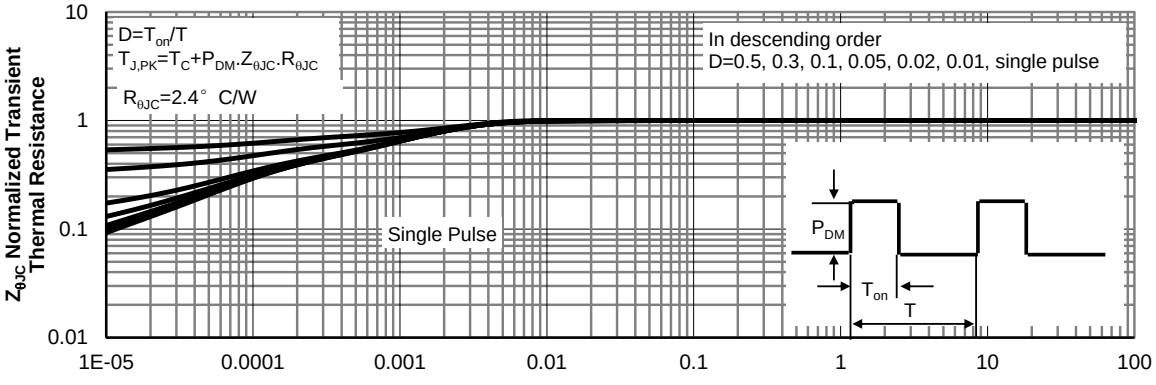


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

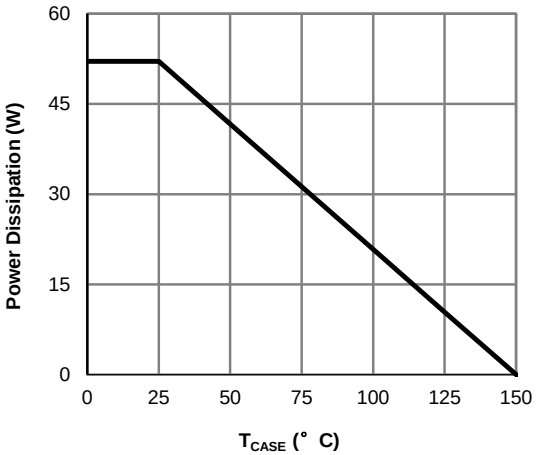


Figure 12: Power De-rating (Note F)

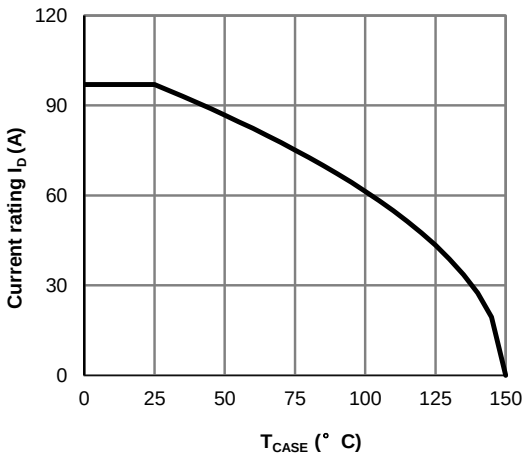


Figure 13: Current De-rating (Note F)

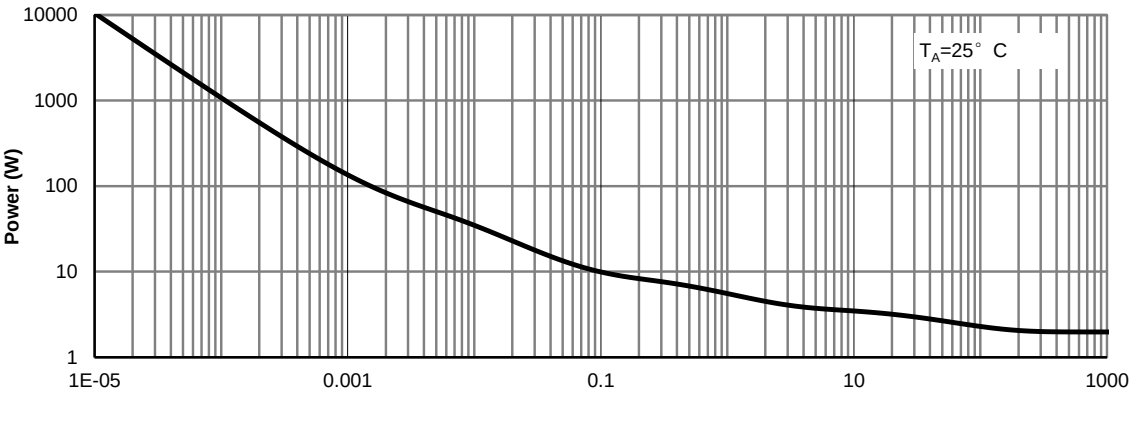


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

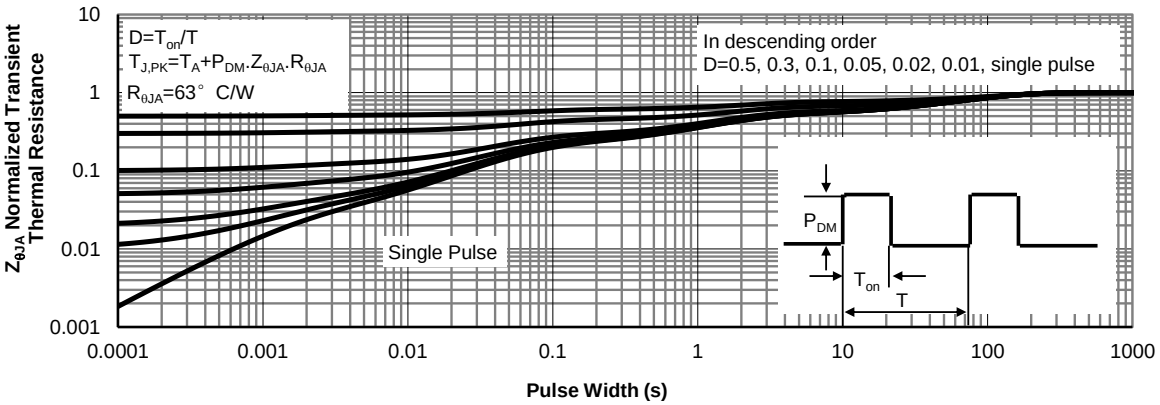


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±12V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	1.1	1.5	1.9	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		3.6	4.4	mΩ
		T_J=125°C		5.4	6.5	
		V_{GS}=4.5V, I_D=20A		4.4	5.6	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		125		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				30	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		1220		pF
C_{oss}	Output Capacitance			260		pF
C_{rss}	Reverse Transfer Capacitance			30		pF
R_g	Gate resistance	f=1MHz	0.9	1.9	2.9	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=20A		17	30	nC
Q_g(4.5V)	Total Gate Charge			7.5	16	nC
Q_{gs}	Gate Source Charge			3.2		nC
Q_{gd}	Gate Drain Charge			1		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		5		ns
t_r	Turn-On Rise Time			18		ns
$t_{D(off)}$	Turn-Off DelayTime			23		ns
t_f	Turn-Off Fall Time			2		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, di/dt=500A/µs		10		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, di/dt=500A/µs		15		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.
H. For application requiring slow >1ms turn-on/turn-off, please consult AOS FAE for proper product selection.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

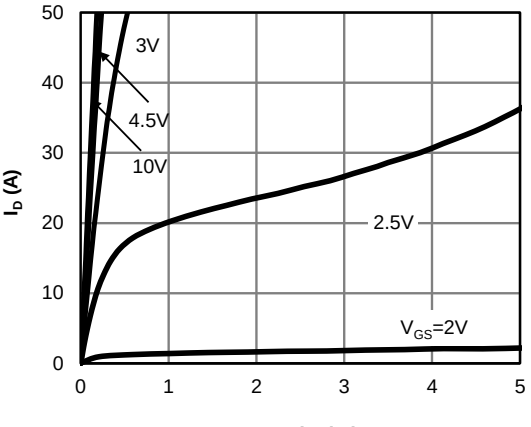


Figure 1: On-Region Characteristics (Note E)

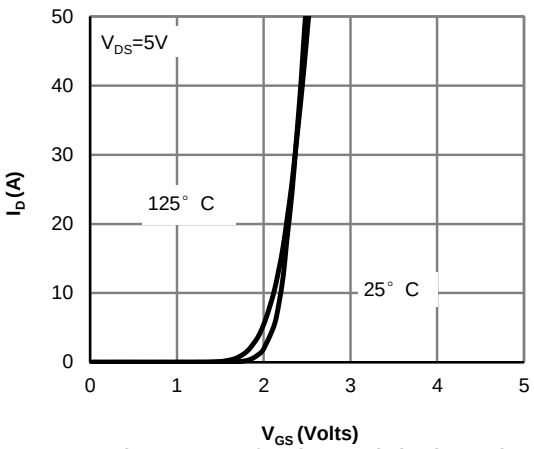


Figure 2: Transfer Characteristics (Note E)

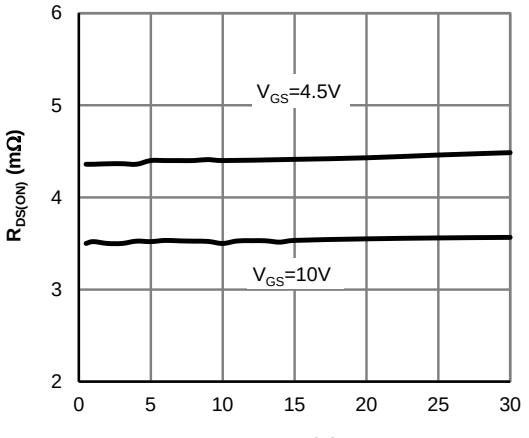


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

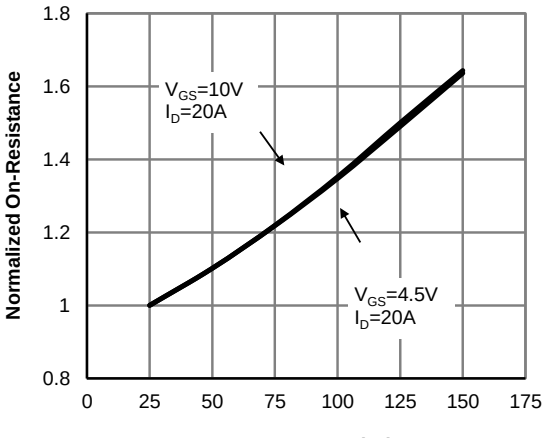


Figure 4: On-Resistance vs. Junction Temperature (Note E)

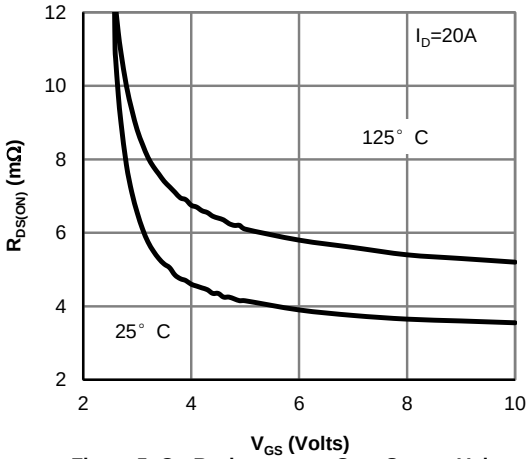


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

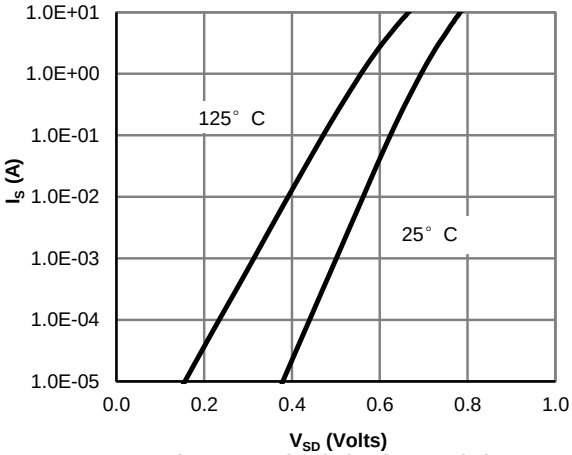


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

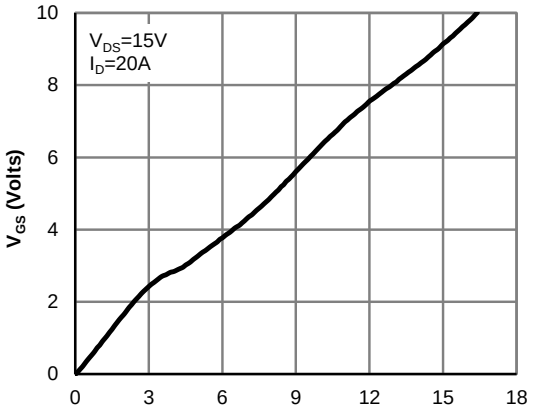


Figure 7: Gate-Charge Characteristics

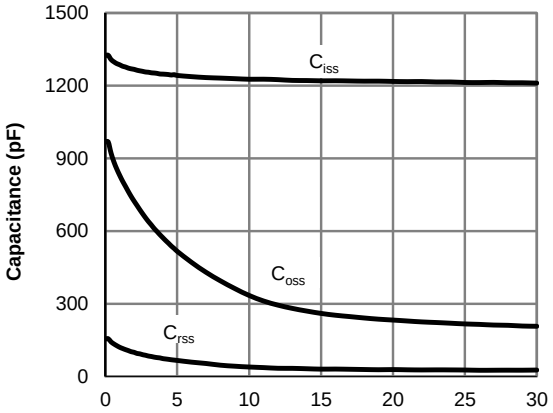


Figure 8: Capacitance Characteristics

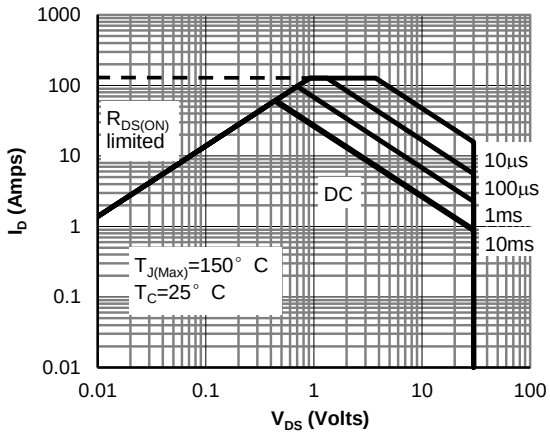


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

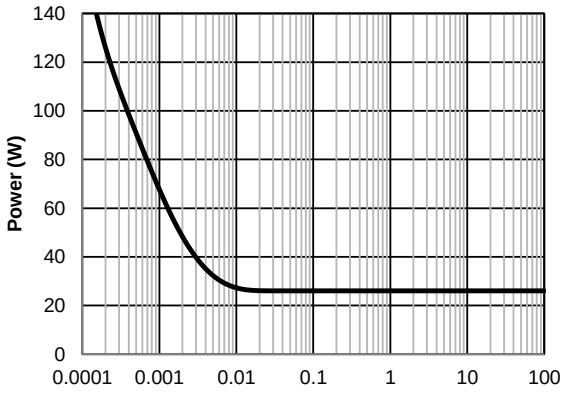


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

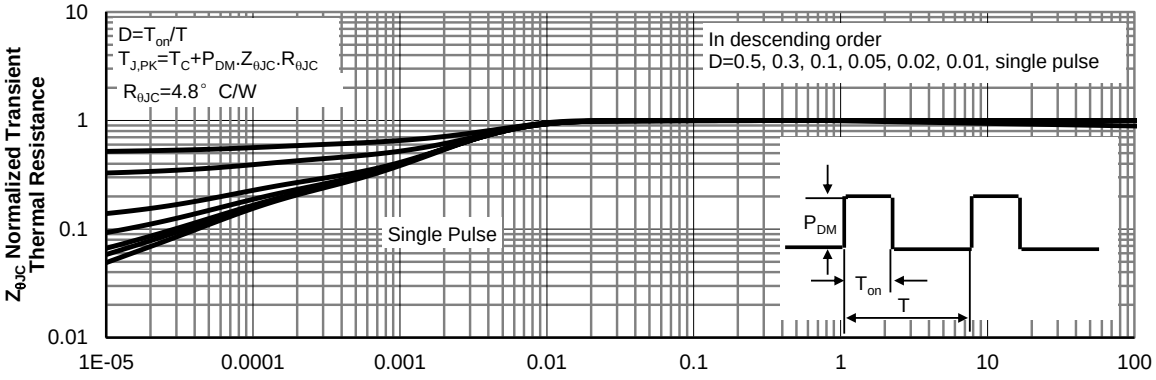


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

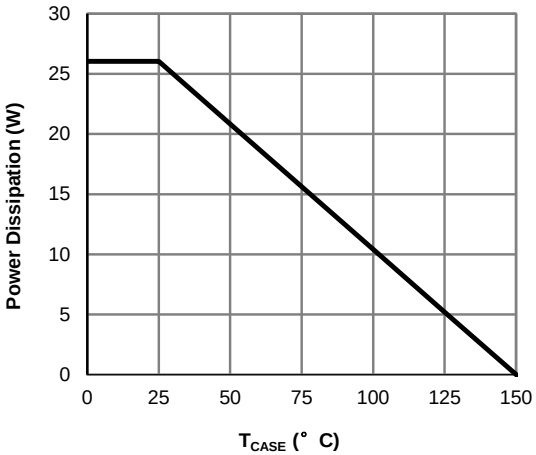


Figure 12: Power De-rating (Note F)

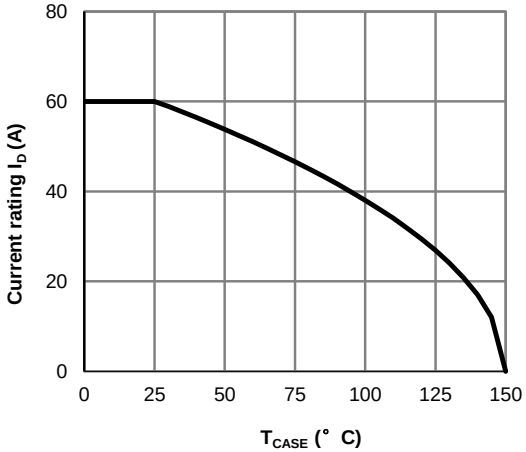


Figure 13: Current De-rating (Note F)

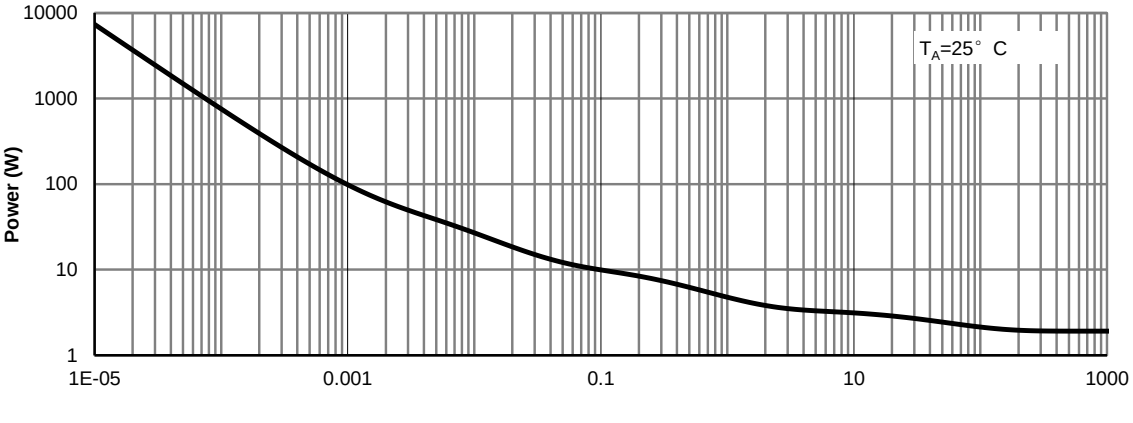


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

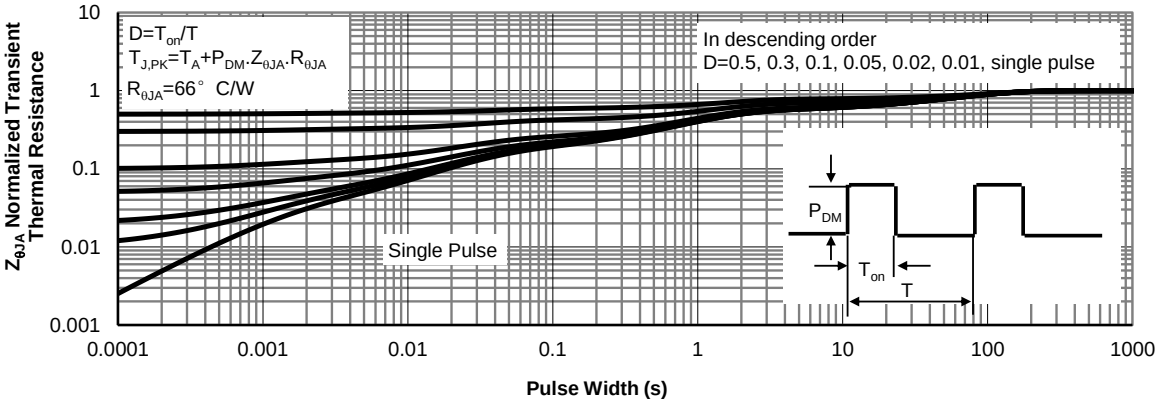


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

Figure A: Gate Charge Test Circuit & Waveforms

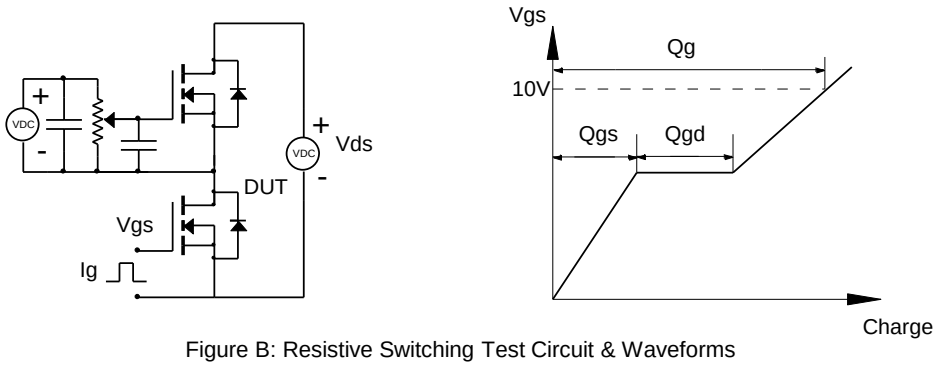


Figure B: Resistive Switching Test Circuit & Waveforms

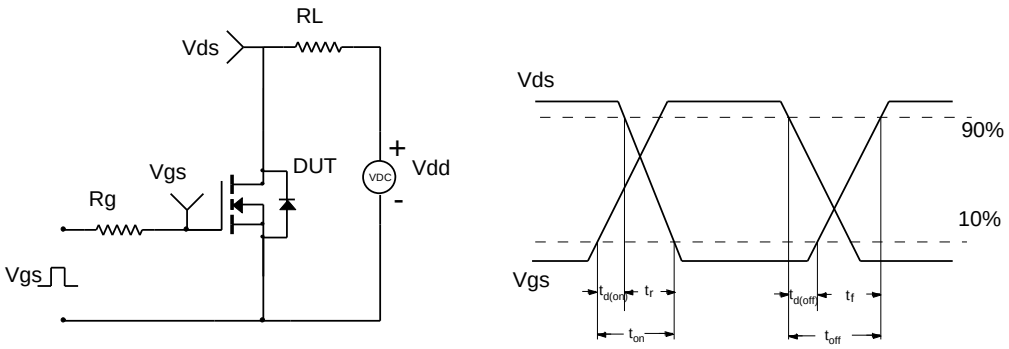


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

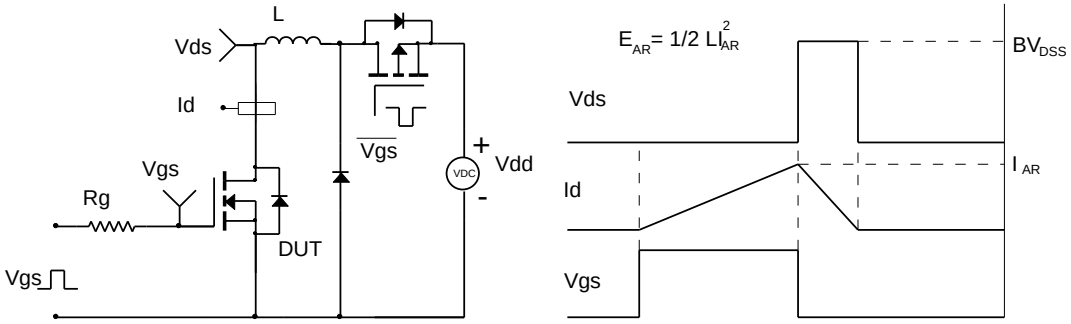


Figure D: Diode Recovery Test Circuit & Waveforms